



Sardar Patel Institute of Technology

Bhavan's Campus, Munshi Nagar, Andheri (West), Mumbai-400058, India

(Autonomous College Affiliated to University of Mumbai)

Re Examination Synoptic

January 2020

Max. Marks: 60

Class: SE

Course Code: CE44/IT42

Name of the Course: Computer Organization and Architecture

Duration: 3 Hrs.

Semester: IV

Branch: Computer/IT

Q. No.		Max. Marks																												
Q.1 A	Write a short note on "The Von Neumann Machine". Diagram- 2 marks Explanation - 4 marks	6																												
Q.1 B	What are the Requirements of Embedded Systems? Explain Possible Organization of an Embedded System Requirements of Embedded Systems[2 marks] Possible Organization of an Embedded System[4 Marks]	6																												
Q.2 A	Draw the flowchart and Multiply 5 x -4 using Booth's Algorithm Flowchart of Booth's Algorithm[2 marks] Multiply 5 x -4 using Booth's Algorithm[4 marks] <div><p>$(5)_{10} \times (-4)_{10}$</p><p>Multiplicand (B) = 0101(5), Multiplier(Q) = 1100(4)</p><table><thead><tr><th>A</th><th>S</th><th>Q_n</th><th></th></tr></thead><tbody><tr><td>0000</td><td>1100</td><td>0</td><td>Initial</td></tr><tr><td>0000</td><td>0110</td><td>0</td><td>Right Shift</td></tr><tr><td>0000</td><td>0011</td><td>0</td><td>Right Shift</td></tr><tr><td>1011</td><td>0011</td><td>0</td><td>A ← A - B</td></tr><tr><td>1101</td><td>1001</td><td>1</td><td>Right Shift</td></tr><tr><td>1110</td><td>1100</td><td>1</td><td>Right Shift</td></tr></tbody></table><p>1110 1100 = 20 (2's complement of 20)</p></div>	A	S	Q _n		0000	1100	0	Initial	0000	0110	0	Right Shift	0000	0011	0	Right Shift	1011	0011	0	A ← A - B	1101	1001	1	Right Shift	1110	1100	1	Right Shift	6
A	S	Q _n																												
0000	1100	0	Initial																											
0000	0110	0	Right Shift																											
0000	0011	0	Right Shift																											
1011	0011	0	A ← A - B																											
1101	1001	1	Right Shift																											
1110	1100	1	Right Shift																											
OR																														
Draw the flowchart of Restoring and Non Restoring Division Algorithm Flowchart of Restoring [3 marks] Flowchart of Non Restoring Division Algorithm [3 Marks]																														

Q.2 B	How IEEE 754 Floating point represents number in Single and Double Precision? Give one example of each. Single Precision Format[1 Marks] Example[2 marks] Double Precision Format[1 Marks] Example[2 marks]	6																							
Q.3 A	How data flow occurs in Indirect cycle and Interrupt Cycle? Data flow occurs in Indirect cycle diagram[1 marks] Explanation [2 marks] Data flow occurs in Indirect cycle diagram[1 marks] Explanation [2 marks]	6																							
Q.3 B	What are the features of RISC and CISC Processor. Why is the need of RISC processor? Features of RISC Processor [2 Marks] Features of CISC Processor [2 Marks] Need of RISC processor[2 Marks] <div>OR</div> What are the functions of Control Unit? What are the control signals associated with control Unit? Functions of Control Unit[3 Marks] Control signals associated with control Unit[3 Marks]	6																							
Q.4 A	Distinguish between the semiconductor types of memory (RAM, PROM, EPROM, EEPROM) with respect to any four relevant points [For e.g., Category(read only/write only), erasure, Write mechanism, Volatility,etc.] for each distinguishing points [2 marks] so total [8 marks] <div>Semiconductor Memory Types</div> <table><thead><tr><th>Memory Type</th><th>Category</th><th>Erasure</th><th>Write Mechanism</th><th>Volatility</th></tr></thead><tbody><tr><td>Random-access memory (RAM)</td><td>Read-write memory</td><td>Electrically, byte-level</td><td>Electrically</td><td>Volatile</td></tr><tr><td>Read-only memory (ROM)</td><td rowspan="2">Read-only memory</td><td rowspan="2">Not possible</td><td>Masks</td><td rowspan="5">Nonvolatile</td></tr><tr><td>Programmable ROM (PROM)</td><td rowspan="4">Electrically</td></tr><tr><td>Erasable PROM (EPROM)</td><td>UV light, chip-level</td></tr><tr><td>Electrically Erasable PROM (EEPROM)</td><td>Electrically, byte-level</td></tr><tr><td>Flash memory</td><td>Electrically, block-level</td></tr></tbody></table>	Memory Type	Category	Erasure	Write Mechanism	Volatility	Random-access memory (RAM)	Read-write memory	Electrically, byte-level	Electrically	Volatile	Read-only memory (ROM)	Read-only memory	Not possible	Masks	Nonvolatile	Programmable ROM (PROM)	Electrically	Erasable PROM (EPROM)	UV light, chip-level	Electrically Erasable PROM (EEPROM)	Electrically, byte-level	Flash memory	Electrically, block-level	8
Memory Type	Category	Erasure	Write Mechanism	Volatility																					
Random-access memory (RAM)	Read-write memory	Electrically, byte-level	Electrically	Volatile																					
Read-only memory (ROM)	Read-only memory	Not possible	Masks	Nonvolatile																					
Programmable ROM (PROM)			Electrically																						
Erasable PROM (EPROM)	UV light, chip-level																								
Electrically Erasable PROM (EEPROM)	Electrically, byte-level																								
Flash memory	Electrically, block-level																								
Q.4 B	What are the drawbacks of Programmed and Interrupt-Driven I/O? Drawbacks of Programmed I/O[2 marks] Drawbacks of Interrupt-Driven I/O[2 marks]	4																							

Q.5 A

Consider a main memory with five page frames and the following sequence of page references: 3, 8, 2, 3, 9, 1, 6, 3, 8, 9, 3, 6, 2, 1, 3.

Which one of the following is true with respect to page replacement policies First-In-First-out (FIFO) and Least Recently Used (LRU)?

- Both incur the same number of page faults
- FIFO incurs 2 more page faults than LRU
- LRU incurs 2 more page faults than FIFO
- FIFO incurs 1 more page faults than LRU

3 marks for each of the algorithms

Number of frames = 5

FIFO

According to FIFO, the page which first comes in the memory will first goes out.

Request	3	8	2	3	9	1	6	3	8	9	3	6	2	1	3
Frame 5						1	1	1	1	1	1	1	1	1	1
Frame 4					9	9	9	9	9	9	9	9	2	2	2
Frame 3			2	2	2	2	2	2	8	8	8	8	8	8	8
Frame 2		8	8	8	8	8	8	3	3	3	3	3	3	3	3
Frame 1	3	3	3	3	3	3	6	6	6	6	6	6	6	6	6
Miss/Hit	Miss	Miss	Miss	Hit	Miss	Miss	Miss	Miss	Miss	Hit	Hit	Hit	Miss	Hit	Hit

Number of Page Faults = 9

Number of hits = 6

LRU

According to LRU, the page which has not been requested for a long time will get replaced with the new one.

Request	3	8	2	3	9	1	6	3	8	9	3	6	2	1	3
Frame 5						1	1	1	1	1	1	1	2	2	2
Frame 4					9	9	9	9	9	9	9	9	9	9	9
Frame 3			2	2	2	2	2	2	8	8	8	8	8	1	1
Frame 2		8	8	8	8	8	6	6	6	6	6	6	6	6	6
Frame 1	3	3	3	3	3	3	3	3	3	3	3	3	3	3	3
Miss/Hit	Miss	Miss	Miss	Hit	Miss	Miss	Hit	Hit	Miss	Hit	Miss	Hit	Miss	Miss	Hit

Number of Page Faults = 9

Number of Hits = 6

The Number of page faults in both the cases is equal therefore the Answer is option (a).

	<p>Consider a memory system that uses a 32-bit address to address at the byte level, plus a cache that uses a 64-byte line size.</p> <p>a. Assume a direct mapped cache with a tag field in the address of 20 bits. Show the address format and determine the following parameters: number of addressable units, number of blocks in main memory, number of lines in cache, size of tag.</p> <p>b. Assume an associative cache. Show the address format and determine the following parameters: number of addressable units, number of blocks in main memory, number of lines in cache, size of tag.</p> <p>a. Address format: Tag = 20 bits; Line = 6 bits; Word = 6 bits. Number of addressable units = 2^{32} bytes; number of blocks in main memory = 2^{26}; Number of lines in cache = $2^6 = 64$; size of tag = 20 bits.</p> <p>b. Address format: Tag = 26 bits; Word = 6 bits. Number of addressable units = 2^{32} bytes; number of blocks in main memory = 2^{26}; Number of lines in cache = undetermined; size of tag = 26 bits.</p> <p>3 marks for each part</p>	6
Q.5 B	<p>What are the different pipeline hazards? Explain each of them.</p> <p>Resource hazards - 2 marks</p> <p>Data hazards - 2 marks</p> <p>Control hazards - 2 marks</p>	6